

## CLAIMS

What is claimed is:

- 1 1. A method comprising:  
2 applying a photoresist layer to a first wafer substrate (wafer);  
3 etching the first wafer;  
4 bonding the first wafer to a second wafer; and  
5 thinning the first wafer to remove an unsupported bevel portion of the  
6 first wafer.
- 1 2. The method of claim 1 further comprising stripping the photoresist layer  
2 after the first wafer has been etched.
- 1 3. The method of claim 1 wherein the photoresist layer is applied to protect  
2 an active portion of the first wafer.
- 1 4. The method of claim 1 wherein the first wafer is etched using a dry  
2 etching method.
- 1 5. The method of claim 1 wherein the first wafer is etched using a wet  
2 etching method.
- 1 6. The method of claim 1 wherein thinning the first wafer comprises  
2 grinding the first wafer.

1 7. A method comprising:  
2 applying a photoresist layer to a first wafer to cover a first component of  
3 the first wafer substrate (wafer);  
4 etching the first wafer;  
5 bonding the first component of the first wafer to a second wafer; and  
6 thinning the first wafer to remove a second unsupported component of  
7 the first wafer.

1 8. The method of claim 7 further comprising stripping the photoresist layer  
2 from the first component after the first wafer has been etched.

1 9. The method of claim 7 wherein the first wafer is etched using a dry  
2 etching method.

1 10. The method of claim 7 wherein the first wafer is etched using a wet  
2 etching method.

1 11. The method of claim 7 wherein thinning the first wafer comprises  
2 grinding the first wafer.

1 12. A method comprising:  
2 removing a first portion of an unsupported component from a wafer  
3 substrate (wafer);

4 bonding an active component of the first wafer to a second wafer; and  
5 thinning the first wafer to remove a second portion of the unsupported  
6 component of the first wafer.

1 13. The method of claim 12 wherein removing the first portion of the  
2 unsupported component comprises:

3 applying a photoresist layer to cover the active component of the first  
4 wafer;

5 etching the first portion of the unsupported component of the first wafer;

1 14. The method of claim 13 further comprising stripping the photoresist layer  
2 from the first component after the first wafer has been etched.

1 15. The method of claim 12 wherein thinning the first wafer comprises  
2 grinding the first wafer.

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